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## FEATURES

■ Conversion Gain: 8.5 dB at 1950MHz

- IIP3: 26.2 dBm at 1950 MHz
- Noise Figure: 9.9dB at 1950MHz
- 15.5dB NF Under 5dBm Blocking
- High Input P1dB
- 47dB Channel-to-Channel Isolation
- 1.25W Power Consumption at 3.3V
- Low Power Mode: <800mW Consumption
- Independent Channel Shutdown Control
- $50 \Omega$ Single-Ended RF and LO Inputs
- LO Input Matched In All Modes
- OdBm LO Drive Level
- Small Package and Solution Size
- $-40^{\circ} \mathrm{C}$ to $105^{\circ} \mathrm{C}$ Operation


## APPLICATIONS

- 3G/4G Wireless Infrastructure Diversity Receivers (LTE, W-CDMA, TD-SCDMA, UMTS, GSM1800)
- Remote Radio Unit
- MIMO Multichannel Receivers
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Dual 1.3 GHz to 2.3 GHz High Dynamic Range Downconverting Mixer DESCRIPTIOn

The LTC®5591 is part of a family of dual-channel high dynamic range, high gain downconverting mixers covering the 600 MHz to 4.5 GHz RF frequency range. The LTC5591 is optimized for 1.3 GHz to 2.3 GHz RF applications. The LO frequency must fall within the 1.4 GHz to 2.1 GHz range for optimum performance. A typical application is a LTE or W-CDMA multichannel or diversity receiver with a 1.7 GHz to 2.2 GHz RF input and low side LO.
The LTC5591's high conversion gain and high dynamic range enable the use of lossy IF filters in high selectivity receiver designs, while minimizing the total solution cost, board space and system-level variation. A low current mode is provided for additional power savings and each of the mixer channels has independent shutdown control. High Dynamic Range Dual Downconverting Mixer Family

| PART NUMBER | RF RANGE | LO RANGE |
| :---: | :---: | :---: |
| LTC5590 | 600 MHz to 1.7 GHz | 700 MHz to 1.5 GHz |
| LTC5591 | 1.3 GHz to 2.3 GHz | $\mathbf{1 . 4 \mathrm { GHz } \text { to } 2 . 1 \mathrm { GHz }}$ |
| LTC5592 | 1.6 GHz to 2.7 GHz | 1.7 GHz to 2.5 GHz |
| LTC5593 | 2.3 GHz to 4.5 GHz | 2.1 GHz to 4.2 GHz |

## TYPICAL APPLICATION



Wideband Conversion Gain, IIP3 and NF vs IF Frequency (Mixer Only, Measured on Evaluation Board)

absolute maximum ratings
(Note 1)
Supply Voltage (VCC) ..... 4.0V
IF Supply Voltage (VCIF) ..... 5.5 V
Enable Voltage (ENA, ENB) ........... -0.3 V to $\mathrm{V}_{\mathrm{CC}}+$ ..... 0.3 V

$\qquad$
Bias Adjust Voltage (IFBA, IFBB) -0.3 V to $\mathrm{V}_{\mathrm{CC}}$ ..... 0.3 V
Power Select Voltage (ISEL) -0.3 V to $\mathrm{V}_{\mathrm{CC}}+0.3 \mathrm{~V}$
LO Input Power (1GHz to 3GHz) ..... 9dBm
LO Input DC Voltage. ..... $\pm 0.1 \mathrm{~V}$
RFA, RFB Input Power (1GHz to 3GHz) ..... 15dBm
RFA, RFB Input DC Voltage ..... $\pm 0.1 \mathrm{~V}$
Operating Temperature Range ( $\mathrm{T}_{\mathrm{C}}$ )

$\qquad$
$-40^{\circ} \mathrm{C}$ to $105^{\circ} \mathrm{C}$
Storage Temperature Range

$\qquad$
$.65^{\circ} \mathrm{C}$ to $150^{\circ} \mathrm{C}$
Junction Temperature ( $\mathrm{T}_{\mathrm{J}}$ ) ..... $150^{\circ} \mathrm{C}$PIn CONFIGURATION


## ORDER InFORMATION

| LEAD FREE FINISH | TAPE AND REEL | PART MARKING | PACKAGE DESCRIPTION | TEMPERATURE RANGE |
| :--- | :--- | :--- | :--- | :--- |
| LTC5591IUH\#PBF | LTC5591IUH\#TRPBF | 5591 | $24-$ Lead $(5 \mathrm{~mm} \times 5 \mathrm{~mm})$ Plastic QFN | $-40^{\circ} \mathrm{C}$ to $105^{\circ} \mathrm{C}$ |

Consult LTC Marketing for parts specified with wider operating temperature ranges.
Consult LTC Marketing for information on non-standard lead based finish parts.
For more information on lead free part marking, go to: http://www.linear.com/leadfree/
For more information on tape and reel specifications, go to: http://www.linear.com/tapeandreel/

## DC ELECTRICAL CHARACTERISTICS <br> $V_{C C}=3.3 \mathrm{~V}, \mathrm{~V}_{\text {CCIF }}=3.3 \mathrm{~V}, \mathrm{ENA}=\mathrm{ENB}=\mathrm{High}, \mathrm{I}_{\mathrm{SEL}}=\mathrm{LOW}, \mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$, <br> unless otherwise noted. Test circuit shown in Figure 1. (Note 2)

| PARAMETER | CONDITIONS | MIN | TYP | MAX | UNITS |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Power Supply Requirements ( $\mathrm{V}_{\text {CCA }}, \mathrm{V}_{\text {CCB }}, \mathrm{V}_{\text {CCIFA }}, \mathrm{V}_{\text {CCIFB }}$ ) |  |  |  |  |  |
| $\mathrm{V}_{\text {CCA }}, \mathrm{V}_{\text {CCB }}$ Supply Voltage (Pins 12, 19) |  | 3.1 | 3.3 | 3.5 | V |
| $\mathrm{V}_{\text {CCIFA }}, \mathrm{V}_{\text {CCIFB }}$ Supply Voltage (Pins 9, 10, 21, 22) |  | 3.1 | 3.3 | 5.3 | V |
| Mixer Supply Current (Pins 12, 19) | Both Channels Enabled |  | 182 | 218 | mA |
| IF Amplifier Supply Current (Pins 9, 10, 21, 22) | Both Channels Enabled |  | 200 | 240 | mA |
| Total Supply Current (Pins 9, 10, 12, 19, 21, 22) | Both Channels Enabled |  | 382 | 458 | mA |
| Total Supply Current - Shutdown | ENA = ENB = Low |  |  | 500 | $\mu \mathrm{A}$ |

Enable Logic Input (ENA, ENB) High = On, Low = Off

| ENA, ENB Input High Voltage (On) |  | 2.5 | V |
| :--- | :--- | :---: | :---: |
| ENA, ENB Input Low Voltage (Off) |  |  | 0.3 |
| ENA, ENB Input Current | -0.3 V to $\mathrm{V}_{\text {CC }}+0.3 \mathrm{~V}$ | -20 | 30 |
| Turn On Time |  | $\mu \mathrm{A}$ |  |
| Turn Off Time |  | 0.9 | $\mu \mathrm{~S}$ |

 unless otherwise noted. Test circuit shown in Figure 1. (Note 2)

| PARAMETER | CONDITIONS | MIN | TYP | MAX | UNITS |
| :--- | :--- | :---: | :---: | :---: | :---: |
| Low Current Mode Logic Input (ISEL) High = Low Power, Low = Normal Power Mode |  |  |  |  |  |
| ISEL Input High Voltage |  | 2.5 |  |  |  |
| ISEL Input Low Voltage |  |  | 0.3 | V |  |
| ISEL Input Current | -0.3 V to $\mathrm{V}_{\text {CC }}+0.3 \mathrm{~V}$ | -20 | 30 | $\mu \mathrm{~A}$ |  |


| Low Current Mode Current Consumption (IsEL $=$ High |  |  |  |  |
| :--- | :--- | :--- | :---: | :---: |
| Mixer Supply Current (Pins 12, 19) | Both Channels Enabled | 119 | 143 | mA |
| IF Amplifier Supply Current (Pins 9, 10, 21, 22) | Both Channels Enabled | 120 | 144 | mA |
| Total Supply Current (Pins 9, 10, 12, 19, 21, 22) | Both Channels Enabled | 239 | 287 | mA |

AC ELECTRICAL CHARACTERISTICS $V_{C C}=3.3 V, V_{C C I F}=3.3 V, E N A=E N B=H i g h, I_{\text {SEL }}=L o w, T_{C}=25^{\circ} \mathrm{C}$,
$P_{\mathrm{LO}}=0 \mathrm{dBm}, \mathrm{P}_{\mathrm{RF}}=-3 \mathrm{dBm}$ ( $\Delta \mathrm{f}=2 \mathrm{MHz}$ for two tone IIP3 tests), unless otherwise noted. Test circuit shown in Figure 1. (Notes 2, 3, 4)


Low Side LO Downmixer Application: $\mathrm{I}_{\mathrm{SEL}}=$ Low, $\mathrm{RF}=1700 \mathrm{MHz}$ to $2300 \mathrm{MHz}, \mathrm{IF}=190 \mathrm{MHz}, \mathrm{f}_{\mathrm{L} 0}=\mathrm{f}_{\mathrm{RF}}-\mathrm{f}_{\mathrm{IF}}$

| PARAMETER | CONDITIONS | MIN | TYP |
| :--- | :--- | :---: | :---: |
| Conversion Gain | $\mathrm{RF}=1750 \mathrm{MHz}$ | 8.7 | MNX |
|  | $\mathrm{RF}=1950 \mathrm{MHz}$ | 7.0 | 8.5 |
| RF $=2150 \mathrm{MHz}$ | dB |  |  |
| Conversion Gain Flatness | $\mathrm{RF}=1950 \pm 30 \mathrm{MHz}, \mathrm{LO}=1760 \mathrm{MHz}, \mathrm{IF}=190 \pm 30 \mathrm{MHz}$ | $\pm 0.25$ | dB |
| Conversion Gain vs Temperature | $\mathrm{T}=-40^{\circ} \mathrm{C}$ to $105^{\circ} \mathrm{C}, \mathrm{RF}=1950 \mathrm{MHz}$ | -0.006 | dB |
| Input 3rd Order Intercept | $\mathrm{RF}=1750 \mathrm{MHz}$ | 26.9 | $\mathrm{~dB} /{ }^{\circ} \mathrm{C}$ |
|  | $\mathrm{RF}=1950 \mathrm{MHz}$ | dBm |  |
|  | $\mathrm{RF}=2150 \mathrm{MHz}$ | 24.0 | 26.2 |
| SSB Noise Figure | $\mathrm{RF}=1750 \mathrm{MHz}$ | 26.2 | dBm |
|  | $\mathrm{RF}=1950 \mathrm{MHz}$ | 9.4 | 9.9 |
|  | $\mathrm{RF}=2150 \mathrm{MHz}$ | 10.8 | dB |


$P_{R F}=-3 \mathrm{dBm}(\Delta f=2 \mathrm{MHz}$ for two tone IIP3 tests), unless otherwise noted. Test circuit shown in Figure 1. (Notes 2, 3)
Low Side LO Downmixer Application: $\mathrm{I}_{\mathrm{SEL}}=$ Low, $R \mathrm{RF}=1700 \mathrm{MHz}$ to $2300 \mathrm{MHz}, \mathrm{IF}=190 \mathrm{MHz}, \mathrm{f}_{\mathrm{L} 0}=\mathrm{f}_{\mathrm{RF}}-\mathrm{f}_{\mathrm{IF}}$

| PARAMETER | CONDITIONS | MIN | TYP | MAX | UNITS |
| :---: | :---: | :---: | :---: | :---: | :---: |
| SSB Noise Figure Under Blocking | $\begin{aligned} & \mathrm{f}_{\mathrm{RF}}=1950 \mathrm{MHz}, \mathrm{f}_{\mathrm{LO}}=1760 \mathrm{MHz}, \mathrm{f}_{\mathrm{BLOCK}}=2050 \mathrm{MHz}, \\ & \mathrm{P}_{\text {BLOCK }}=5 \mathrm{dBm} \\ & \mathrm{P}_{\text {BLOCK }}=10 \mathrm{dBm} \end{aligned}$ |  | $\begin{aligned} & 15.5 \\ & 20.2 \end{aligned}$ |  | dB dB |
| 2RF-2LO Output Spurious Product $\left(f_{\mathrm{RF}}=f_{L O}+f_{\mathrm{IF}} / 2\right)$ | $\begin{aligned} & f_{\mathrm{RF}}=1855 \mathrm{MHz} \text { at }-10 \mathrm{dBm}, \mathrm{f}_{\mathrm{LO}}=1760 \mathrm{MHz}, \\ & \mathrm{f}_{\mathrm{IF}}=190 \mathrm{MHz} \end{aligned}$ |  | -69 |  | dBC |
| 3RF-3LO Output Spurious Product $\left(f_{\mathrm{RF}}=\mathrm{f}_{\mathrm{LO}}+\mathrm{f}_{\mathrm{IF}} / 3\right)$ | $\begin{aligned} & \mathrm{f}_{\mathrm{RF}}=1823.33 \mathrm{MHz} \text { at }-10 \mathrm{dBm}, \mathrm{f}_{\mathrm{LO}}=1760 \mathrm{MHz}, \\ & \mathrm{f}_{\mathrm{IF}}=190 \mathrm{MHz} \end{aligned}$ |  | -74 |  | dBC |
| Input 1dB Compression | $\begin{aligned} & f_{\mathrm{RF}}=1950 \mathrm{MHz}, \mathrm{~V}_{\text {CCIF }}=3.3 \mathrm{~V} \\ & \mathrm{f}_{\mathrm{RF}}=1950 \mathrm{MHz}, \mathrm{~V}_{\text {CCIF }}=5 \mathrm{~V} \end{aligned}$ |  | $\begin{aligned} & 10.7 \\ & 13.9 \end{aligned}$ |  | $\begin{aligned} & \mathrm{dBm} \\ & \mathrm{dBm} \end{aligned}$ |

Low Power Mode, Low Side LO Downmixer Application: $\mathrm{I}_{\text {SEL }}=$ High, $\mathrm{RF}=1700 \mathrm{MHz}$ to 2300 MHz , IF $=190 \mathrm{MHz}, \mathrm{f}_{\mathrm{L} 0}=\mathrm{f}_{\mathrm{RF}}-\mathrm{f}_{\mathrm{IF}}$

| PARAMETER | CONDITIONS | MIN | TYP |
| :--- | :--- | ---: | ---: |
| Conversion Gain | $\mathrm{RF}=1950 \mathrm{MHz}$ | 7.2 | UNITS |
| Input 3rd Order Intercept | $\mathrm{RF}=1950 \mathrm{MHz}$ | 21.4 | dB |
| SSB Noise Figure | $\mathrm{RF}=1950 \mathrm{MHz}$ | 10.3 | dBm |
| Input 1dB Compression | $\mathrm{RF}=1950 \mathrm{MHz}, \mathrm{V}_{\text {CCIF }}=3.3 \mathrm{~V}$ | dB |  |
|  | $\mathrm{RF}=1950 \mathrm{MHz}, \mathrm{V}_{\text {CCIF }}=5 \mathrm{~V}$ | 10.7 | dBm |

High Side LO Downmixer Application: $\mathrm{I}_{\mathrm{SEL}}=$ Low, $\mathrm{RF}=1300 \mathrm{MHz}$ to $1800 \mathrm{MHz}, \mathrm{IF}=190 \mathrm{MHz}, \mathrm{f}_{\mathrm{L} 0}=\mathrm{f}_{\mathrm{RF}}+\mathrm{f}_{\mathrm{IF}}$


Note 1: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime.
Note 2: The LTC5591 is guaranteed functional over the case operating temperature range of $-40^{\circ} \mathrm{C}$ to $105^{\circ} \mathrm{C}$. $\left(\theta_{\mathrm{Jc}}=7^{\circ} \mathrm{C} / \mathrm{W}\right)$

Note 3: SSB Noise Figure measured with a small-signal noise source, bandpass filter and 6dB matching pad on RF input, bandpass filter and 6 dB matching pad on the LO input, and no other RF signals applied.
Note 4: Channel $A$ to channel $B$ isolation is measured as the relative IF output power of channel $B$ to channel $A$, with the RF input signal applied to channel $A$. The RF input of channel $B$ is $50 \Omega$ terminated and both mixers are enabled.

## TYPICAL AC PGRFORMANCE CHARACTERISTICS <br> Low Side LO

$\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V}, \mathrm{~V}_{\text {CCIF }}=3.3 \mathrm{~V}, E N A=E N B=$ High, $\mathrm{I}_{\mathrm{SEL}}=$ Low, $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}, \mathrm{P}_{\mathrm{LO}}=0 \mathrm{dBm}, \mathrm{P}_{\mathrm{RF}}=-3 \mathrm{dBm}(-3 \mathrm{dBm} /$ tone for two-tone IIP3 tests, $\Delta f=2 \mathrm{MHz}), \mathrm{IF}=190 \mathrm{MHz}$, unless otherwise noted. Test circuit shown in Figure 1.


## TYPICAL AC PGRFORMANCE CHARACTERISTICS <br> Low Side LO (continued)

$\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V}, \mathrm{~V}_{\text {CCIF }}=3.3 \mathrm{~V}, \mathrm{ENA}=\mathrm{ENB}=\mathrm{High}, \mathrm{I}_{\mathrm{SEL}}=\mathrm{Low}, \mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}, \mathrm{P}_{\mathrm{L} O}=0 \mathrm{dBm}, \mathrm{P}_{\mathrm{RF}}=-3 \mathrm{dBm}(-3 \mathrm{dBm} /$ tone for two-tone IIP3 tests, $\Delta f=2 \mathrm{MHz}), \mathrm{IF}=190 \mathrm{MHz}$, unless otherwise noted. Test circuit shown in Figure 1.


5591 G10
SSB Noise Figure vs RF Blocker Power


5591 G13

Single-Tone IF Output Power, $2 \times 2$ and $3 \times 3$ Spurs vs RF Input Power


LO Leakage vs LO Frequency


5591 G14
$2 \times 2$ and $3 \times 3$ Spurs vs LO Power


5591 G12

RF Isolation vs RF Frequency


5591 G15


5591 G16


SSB Noise Figure Distribution

$\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V}, \mathrm{~V}_{\text {CCIF }}=3.3 \mathrm{~V}, \mathrm{ENA}=\mathrm{ENB}=\mathrm{High}, \mathrm{I}_{\mathrm{SEL}}=\mathrm{High}, \mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}, \mathrm{P}_{\mathrm{LO}}=\mathrm{OdBm}, \mathrm{P}_{\mathrm{RF}}=-3 \mathrm{dBm}(-3 \mathrm{dBm} /$ tone for two-tone IIP3 tests, $\Delta f=2 M H z), I F=190 \mathrm{MHz}$, unless otherwise noted. Test circuit shown in Figure 1.


## TYPICAL AC PERFORMANCE CHARACTERISTICS <br> High Side LO

$\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V}, \mathrm{~V}_{\mathrm{CCIF}}=3.3 \mathrm{~V}, E N A=E N B=$ High, $\mathrm{I}_{\mathrm{SEL}}=$ Low, $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}, \mathrm{P}_{\mathrm{LO}}=0 \mathrm{dBm}, \mathrm{P}_{\mathrm{RF}}=-3 \mathrm{dBm}(-3 \mathrm{dBm} /$ tone for two-tone IIP3 tests, $\Delta f=2 M H z), I F=190 \mathrm{MHz}$, unless otherwise noted. Test circuit shown in Figure 1 .


TYPICAL DC PGRFORMANCE CHARACTERISTICS ENA = eNB = High, test tirruit shown in figure 1 .
$I_{\text {SEL }}=$ Low


5591 G37
$I_{\text {SEL }}=$ High

$V_{\text {cc }}$ Supply Current vs Supply Voltage (Mixer and LO Amplifier)
$V_{\text {CCIF }}$ Supply Current vs Supply Voltage (IF Amplifier)


5591 G41

Total Supply Current vs Temperature ( $V_{\text {CC }}+V_{\text {CCIF }}$ )


5591639

Total Supply Current vs Temperature ( $\mathrm{V}_{\text {CC }}+\mathrm{V}_{\text {CCIF }}$ )


595

## PIn fUnCTIONS

RFA, RFB (Pins 1, 6): Single-Ended RF Inputs for Channels $A$ and $B$. These pins are internally connected to the primary sides of the RF input transformers, which have low DC resistance to ground. Series DC-blocking capacitors should be used to avoid damage to the integrated transformer when DC voltage is present at the RF inputs. The RF inputs are impedance matched when the LO input is driven with a $0 \pm 6 \mathrm{dBm}$ source between 1.4 GHz and 2.1 GHz and the channels are enabled.

CTA, CTB (Pins 2, 5): RF Transformer Secondary CenterTap on Channels A and B. These pins may require bypass capacitors to ground to optimize IIP3 performance. Each pin has an internally generated bias voltage of 1.2 V and must be DC-isolated from ground and $\mathrm{V}_{\mathrm{CC}}$.
GND (Pins 3, 4, 7, 13, 15, 24, Exposed Pad Pin 25): Ground. These pins must be soldered to the RF ground plane on the circuit board. The exposed pad metal of the package provides both electrical contact to ground and good thermal contact to the printed circuit board.
IFGNDB, IFGNDA (Pins 8, 23): DC Ground Returns for the IF Amplifiers. These pins must be connected to ground to complete the DC current paths for the IF amplifiers. Chip inductors may be used to tune LO-IF and RF-IF leakage. Typical DC current is 100 mA for each pin.

IFB ${ }^{+}$, IFB${ }^{-}$, IFA ${ }^{-}$, IFA ${ }^{+}$(Pins 9, 10, 21, 22): Open-Collector Differential Outputs for the IF Amplifiers of Channels $B$ and $A$. These pins must be connected to a DC supply through impedance matching inductors, or transformer center-taps. Typical DC current consumption is 50 mA into each pin.

IFBB, IFBA (Pins 11, 20): Bias Adjust Pins for the IF Amplifiers. These pins allow independent adjustment of the internal IF buffer currents for channels B and A, respectively. The typical DC voltage on these pins is 2.2 V . If not used, these pins must be DC isolated from ground and $\mathrm{V}_{\mathrm{CC}}$.
$V_{\text {CCB }}$ and $V_{\text {CCA }}$ (Pins 12, 19): Power Supply Pins for the LO Buffers and Bias Circuits. These pins must be connected to a regulated 3.3 V supply with bypass capacitors located close to the pins. Typical current consumption is 91mA per pin.

ENB, ENA (Pins 14, 17): Enable Pins. These pins allow Channels B and A, respectively, to be independently enabled. An applied voltage of greater than 2.5 V activates the associated channel while a voltage of less than 0.3 V disables the channel. Typical input current is less than $10 \mu \mathrm{~A}$. These pins must not be allowed to float.

LO (Pin 16): Single-Ended Local Oscillator Input. This pin is internally connected to the primary side of the LO input transformer and has a low DC resistance to ground. Series DC-blocking capacitors should be used to avoid damage to the integrated transformer when DC voltage is present at the LO input. The LO input is internally matched to $50 \Omega$ for all states of ENA and ENB.

Isel (Pin 18): Low Current Select Pin. When this pin is pulled low ( $<0.3 \mathrm{~V}$ ), both mixer channels are biased at the normal current level for best RF performance. When greater than 2.5 V is applied, both channels operate at reduced current, which provides reasonable performance at lower power consumption. This pin must not be allowed to float.

## BLOCK DIAGRAM



## LTC5591

test circuit


| L1, L2 vs IF FREQUENCIES |  |
| :---: | :---: |
| IF (MHz) | L1, L2 (nH) |
| 140 | 270 |
| 190 | 150 |
| 240 | 100 |
| 300 | 56 |
| 380 | 33 |


| REF DES | VALUE | SIZE | VENDOR |
| :---: | :---: | :---: | :---: |
| C1A, C1B, <br> C8A, C8B | 2.7 pF | 0402 | AVX |
| C2 | 4.7 pF | 0402 | AVX |
| C3A, C3B <br> C5A, C5B | $22 p F$ | 0402 | AVX |
| C4, C6 | $1 \mu F$ | 0603 | AVX |
| C7A, C7B | 1000 pF | 0402 | AVX |
| L1, L2 | 150 nH | 0603 | Coilcraft |
| T1A, T1B | TC1-1W-7ALN+ |  | Mini-Circuits |

Figure 1. Standard Test Circuit Schematic (190MHz IF)

## APPLICATIONS INFORMATION

## Introduction

The LTC5591 consists of two identical mixer channels driven by a common LO input signal. Each high linearity mixer consists of a passive double-balanced mixer core, IF buffer amplifier, LO buffer amplifier and bias/enable circuits. See the Pin Functions and Block Diagram sections for a description of each pin. Each of the mixers can be shutdown independently to reduce power consumption and low current mode can be selected that allows a trade-off between performance and power consumption. The RFand LO inputs are single-ended and are internally matched to $50 \Omega$. Low side or high side LO injection can be used. The IF outputs are differential. The evaluation circuit, shown in Figure 1, utilizes bandpass IF output matching and an IF transformer to realize a $50 \Omega$ single-ended IF output. The evaluation board layout is shown in Figure 2.


Figure 2. Evaluation Board Layout

## RF Inputs

The RF inputs of channels A and B are identical. The RF input of channel $A$, shown in Figure 3, is connected to the primary winding of an integrated transformer. $\mathrm{A} 50 \Omega$ match is realized when a series external capacitor, C 1 A , is connected to the RF input. C1A is also needed for DC blocking
if the source has DC voltage present, since the primary side of the RF transformer is internally DC-grounded. The DC resistance of the primary is approximately $3.6 \Omega$.

The secondary winding of the RF transformer is internally connected to the channel A passive mixer core. The center-tap of the transformer secondary is connected to Pin 2 (CTA) to allow the connection of bypass capacitor, C8A. The value of C8A can be adjusted to improve the channel-to-channel isolation at specific RF operation frequency with minor impact to conversion gain, linearity and noise performance. The channel-to-channel isolation performance with different values of C8A is given in Figure 4. When used, it should be located within 2 mm of Pin 2 for proper high frequency decoupling. The nominal DC voltage on the CTA pin is 1.2 V .


Figure 3. Channel A RF Input Schematic


Figure 4. Channel-to-Channel Isolation vs C8 Values

## APPLICATIONS InFORMATION

For the RF inputs to be properly matched, the appropriate LO signal must be applied to the LO input. A broadband input match is realized with $\mathrm{C1A}=2.2 \mathrm{pF}$. The measured input return loss is shown in Figure 4 for LO frequencies of $1.4 \mathrm{GHz}, 1.75 \mathrm{GHz}$ and 2 GHz . These LO frequencies correspond to lower, middle and upper values in the LO range. As shown in Figure 5, the RF input impedance is dependent on LO frequency, although a single value of C1A is adequate to cover the 1.3 GHz to 2.3 GHz RF band.


Figure 5. RF Port Return Loss
The RF input impedance and input reflection coefficient, versus RF frequency, are listed in Table 1. The reference plane for this data is pin 1 of the IC, with no external matching, and the LO is driven at 1.75 GHz .

Table 1. RF Input Impedance and S11
(at Pin 1, No External Matching, $\mathrm{f}_{\mathrm{LO}}=1.75 \mathrm{GHz}$ )

| FREQUENCY <br> (GHz) | RF INPUT <br> IMPEDANCE | S11 |  |
| :---: | :---: | :---: | :---: |
|  |  | ANGLE |  |
| 1.0 | $25.3+\mathrm{j} 34.6$ | 0.51 | 100.8 |
| 1.2 | $33.7+\mathrm{j} 38.7$ | 0.46 | 88.1 |
| 1.4 | $43.8+\mathrm{j} 38.6$ | 0.39 | 76.8 |
| 1.6 | $56.0+\mathrm{j} 33.5$ | 0.31 | 62.3 |
| 1.8 | $48.1+\mathrm{j} 9.1$ | 0.09 | 96.4 |
| 2.0 | $38.5+\mathrm{j} 21.4$ | 0.27 | 104.6 |
| 2.2 | $40.1+\mathrm{j} 28.3$ | 0.32 | 91.8 |
| 2.4 | $44.0+\mathrm{j} 34.7$ | 0.35 | 79.6 |
| 2.6 | $52.1+\mathrm{j} 40.7$ | 0.37 | 65.3 |
| 2.8 | $64.1+\mathrm{j} 44.1$ | 0.38 | 51.2 |
| 3.0 | $78.8+\mathrm{j} 42.0$ | 0.38 | 37.5 |

## LO Input

The LO input, shown in Figure 6, is connected to the primary winding of an integrated transformer. A $50 \Omega$ impedance match is realized at the LO port by adding an external series capacitor, C2. This capacitor is also needed for DC blocking if the LO source has DC voltage present, since the primary side of the LO transformer is DC-grounded internally. The DC resistance of the primary is approximately $4.1 \Omega$.


Figure 6. LO Input Schematic
The secondary of the transformer drives a pair of high speed limiting differential amplifiers for channels A and B. The LTC5591's LO amplifiers are optimized for the 1.4GHz to 2.1 GHz LO frequency range; however, LO frequencies outside this frequency range may be used with degraded performance.

The $L 0$ port is always $50 \Omega$ matched when $V_{C C}$ is applied, even when one or both of the channels is disabled. This helps to reduce frequency pulling of the LO source when

## APPLICATIONS INFORMATION

the mixer is switched between different operating states. Figure 7 illustrates the LO port return loss for the different operating modes.


Figure 7. LO Input Return Loss

The nominal LO input level is OdBm, though the limiting amplifiers will deliver excellent performance over $a \pm 6 \mathrm{dBm}$ input power range. Table 2 lists the LO input impedance and input reflection coefficient versus frequency.

Table 2. LO Input Impedance vs Frequency
(at Pin 16, No External Matching, ENA = ENB = High)

| FREQUENCY <br> (GHz) | INPUT <br> IMPEDANCE | S11 |  |
| :---: | :---: | :---: | :---: |
|  | MAG | ANGLE |  |
| 1.0 | $39.4+\mathrm{j} 46.4$ | 0.47 | 75.5 |
| 1.2 | $55.3+\mathrm{j} 40.8$ | 0.36 | 61.4 |
| 1.4 | $61.9+\mathrm{j} 26.8$ | 0.25 | 52.6 |
| 1.6 | $56.5+\mathrm{j} 16.1$ | 0.16 | 59.5 |
| 1.8 | $47.6+\mathrm{j} 14.0$ | 0.14 | 91.6 |
| 2.0 | $41.6+\mathrm{j} 18.0$ | 0.21 | 103.9 |
| 2.2 | $38.4+\mathrm{j} 23.5$ | 0.29 | 101.5 |
| 2.4 | $37.1+\mathrm{j} 30.7$ | 0.36 | 93.3 |
| 2.6 | $38.4+\mathrm{j} 38.3$ | 0.42 | 83.3 |
| 2.8 | $42.0+\mathrm{j} 47.6$ | 0.47 | 72.2 |
| 3.0 | $48.6+\mathrm{j} 56.1$ | 0.49 | 61.8 |

## IF Outputs

The IF amplifiers in channels $A$ and $B$ are identical. The IF amplifier for channel A, shown in Figure 8, has differential open collector outputs (IFA+ and IFA ${ }^{-}$), a DC ground
return pin (IFGNDA), and a pin for adjusting the internal bias (IFBA). The IF outputs must be biased at the supply voltage ( $\mathrm{V}_{\text {CCIFA }}$ ), which is applied through matching inductors L1A and L2A. Alternatively, the IF outputs can be biased through the center tap of a transformer (T1A). The common node of L1A and L2A can be connected to the center tap of the transformer. Each IF output pin draws approximately 50 mA of DC supply current ( 100 mA total). An external load resistor, R2A, can be used to improve impedance matching if desired.
IFGNDA (Pin 23) must be grounded or the amplifier will not draw DC current. Inductor L3A may improve LO-IF and RF-IF leakage performance in some applications, but is otherwise not necessary. Inductors should have small resistance for DC. High DC resistance in L3A will reduce the IF amplifier supply current, which will degrade RF performance.


Figure 8. IF Amplifier Schematic with Bandpass Match

For optimum single-ended performance, the differential IF output must be combined through an external IF transformer or a discrete IF balun circuit. The evaluation board (see Figures 1 and 2) uses a 4:1 IF transformer for impedance transformation and differential to single-ended conversion. It is also possible to eliminatethe IFtransformer and drive differential filters or amplifiers directly.

## APPLICATIONS InFORMATION

At IF frequencies, the IF output impedance can be modeled as $300 \Omega$ in parallel with 2.3pF. The equivalent small-signal model, including bondwire inductance, is shown in Figure 9. Frequency-dependent differential IF output impedance is listed in Table 3. This data is referenced to the package pins (with no external components) and includes the effects of IC and package parasitics.


Figure 9. IF Output Small-Signal Model

## Bandpass IF Matching

The bandpass IF matching configuration, shown in Figures 1 and 8 , is best suited for IF frequencies in the 90 MHz to 500 MHz range. Resistor R2A may be used to reduce the IF output resistance for greater bandwidth and inductors L1A and L2A resonate with the internal IF output capacitance at the desired IF frequency. The value of L1A, L2A can be estimated as follows:

$$
L 1 A=L 2 A=\frac{1}{\left[\left(2 \pi f_{I F}\right)^{2} \cdot 2 \cdot C_{I F}\right]}
$$

where $\mathrm{C}_{\mathrm{IF}}$ is the internal IF capacitance (listed in Table 3).
Table 3. IF Output Impedance vs Frequency

| FREQUENCY (MHz) | DIFFERENTIAL OUTPUT <br> IMPEDANCE $\left(\mathbf{R}_{\text {IF }} \\| \mathbf{X I F}_{\text {IF }}\left(\mathbf{C}_{\text {IF }}\right)\right)$ |
| :---: | :---: |
| 90 | $321 \\|-\mathrm{j} 769(2.3 p F)$ |
| 140 | $307 \\|-\mathrm{j} 494(2.3 p F)$ |
| 190 | $300 \\|-\mathrm{j} 364(2.3 p F)$ |
| 240 | $292 \\|-\mathrm{j} 286(2.3 p F)$ |
| 300 | $285 \\|-\mathrm{j} 225(2.4 \mathrm{pF})$ |
| 380 | $276 \\|-\mathrm{j} 177(2.4 \mathrm{pF})$ |
| 500 | $264 \\|-\mathrm{j} 122(2.6 p F)$ |

Values of L1A and L2A are tabulated in Figure 1 for various IF frequencies. The measured IF output return loss for bandpass IF matching is plotted in Figure 10.


5591 F10
Figure 10. IF Output Return Loss with Bandpass Matching

## Lowpass IF Matching

For IF frequencies below 90 MHz , the inductance values become unreasonably high and the lowpass topology shown in Figure 11 is preferred. This topology also can provide improved RF to IF and LO to IF isolation. VCCIFA is supplied through the center tap of the $4: 1$ transformer. A lowpass impedance transformation is realized by shunt elements R2A and C9A (in parallel with the internal RIF and CIF), and series inductors L1A and L2A. Resistor R2A is used to reduce the IF output resistance for greater bandwidth, or it can be deleted for the highest conversion gain. The final impedance transformation to $50 \Omega$ is realized by transformer T1A. The measured IF output return loss for


Figure 11. IF Output with Lowpass Matching

## APPLICATIONS INFORMATION

lowpass IF matching with R2A and C9A open is plotted in Figure 12. The LTC5591 demo board (see Figure 2) has been laid out to accommodate this matching topology with only minor modifications.


5591 F12
Figure 12. IF Output Return Loss with Lowpass Matching

## IF Amplifier Bias

The IF amplifier delivers excellent performance with $\mathrm{V}_{\text {CCIF }}$ $=3.3 \mathrm{~V}$, which allows a single supply to be used for $\mathrm{V}_{\text {CC }}$ and $\mathrm{V}_{\text {CCIF }}$. At $\mathrm{V}_{\text {CCIF }}=3.3 \mathrm{~V}$, the RF input P1dB of the mixer is limited by the output voltage swing. For higher P1dB, in this case, resistor R2A (Figure 7) can be used to reduce the output impedance and thus the voltage swing, thus improving P1dB. The trade-off for improved P1dB will be lower conversion gain.

With $\mathrm{V}_{\text {CCIF }}$ increased to 5 V the P1dB increases by over 3 dB , at the expense of higher power consumption. Mixer P1dB performance at 1950MHz is tabulated in Table 4 for $V_{\text {CCIF }}$ values of 3.3 V and 5 V . For the highest conversion gain, high-Q wire-wound chip inductors are recommended for L1A and L2A, especially when using $\mathrm{V}_{\text {CCIF }}=3.3 \mathrm{~V}$. Low cost multilayer chip inductors may be substituted, with a slight reduction in conversion gain.

Table 4. Performance Comparison with $\mathrm{V}_{\text {clif }}=3.3 \mathrm{~V}$ and 5 V ( $\mathrm{RF}=1950 \mathrm{MHz}$, Low Side LO, IF = 190MHz, ENA = ENB $=$ High )

| $\mathbf{V}_{\text {CCIF }}$ <br> $(\mathbf{V})$ | R2A <br> $(\boldsymbol{\Omega})$ | $\mathbf{I}_{\text {CCIF }}$ <br> $(\mathbf{m A})$ | $\mathbf{G}_{\mathbf{C}}$ <br> $(\mathbf{d B})$ | P1dB <br> $(\mathbf{d B m})$ | IIP3 <br> $(\mathbf{d B m})$ | $\mathbf{N F}$ <br> $(\mathbf{d B})$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | 0 pen | 200 | 8.5 | 10.7 | 26.2 | 9.9 |
|  | 1 k | 200 | 7.4 | 11.5 | 26.5 | 9.9 |
| 5 | 0 pen | 207 | 8.4 | 13.9 | 26.7 | 10.1 |

The IFBA pin (Pin 20) is available for reducing the DC current consumption of the IF amplifier, at the expense of IIP3. The nominal DC voltage at Pin 20 is 2.1 V , and this pin should be left open-circuited for optimum performance. The internal bias circuit produces a 4 mA reference for the IF amplifier, which causes the amplifier to draw approximately 100 mA . If resistor R1A is connected to Pin 20 as shown in Figure 8, a portion of the reference current can be shunted to ground, resulting in reduced IF amplifier current. For example, R1A $=470 \Omega$ will shunt away 1.4 mA from Pin 20 and the IF amplifier current will be reduced by $35 \%$ to approximately 65 mA . Table 5 summarizes RF performance versus total IF amplifier current when both channels are enabled.

Table 5. Mixer Performance with Reduced IF Amplifier Current RF $=1950 \mathrm{MHz}$, Low Side LO, IF $=190 \mathrm{MHz}, \mathrm{V}_{\text {CC }}=\mathrm{V}_{\text {clif }}=3.3 \mathrm{~V}$

| R1A, R1B | $\mathbf{I}_{\mathbf{C C I F}}$ <br> $(\mathbf{m A})$ | $\mathbf{G}_{\mathbf{C}}$ <br> $(\mathbf{d B})$ | IIP3 <br> $(\mathbf{d B m})$ | $\mathbf{P 1 d B}$ <br> $(\mathbf{d B m})$ | $\mathbf{N F}$ <br> $(\mathbf{d B})$ |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Open | 200 | 8.5 | 26.2 | 10.7 | 9.9 |
| $3.3 \mathrm{k} \Omega$ | 176 | 8.4 | 25.7 | 10.8 | 9.9 |
| $1.0 \mathrm{k} \Omega$ | 151 | 8.1 | 24.7 | 10.9 | 9.9 |
| $470 \Omega$ | 130 | 7.9 | 23.7 | 10.9 | 9.9 |

$R \mathrm{RF}=1600 \mathrm{MHz}$, High Side LO, IF $=190 \mathrm{MHz}, \mathrm{V}_{\text {CC }}=\mathrm{V}_{\text {CCIF }}=3.3 \mathrm{~V}$

| R1A, R1B | $\mathbf{I} \mathbf{C C I F}$ <br> $(\mathbf{m A})$ | $\mathbf{G C}_{\mathbf{C}}$ <br> $(\mathbf{d B})$ | IIP3 <br> $(\mathbf{d B m})$ | P1dB <br> $(\mathbf{d B m})$ | $\mathbf{N F}$ <br> $(\mathbf{d B})$ |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Open | 200 | 8.6 | 24.6 | 10.2 | 10.2 |
| $3.3 \mathrm{k} \Omega$ | 176 | 8.4 | 24.3 | 10.4 | 10.3 |
| $1.0 \mathrm{k} \Omega$ | 151 | 8.1 | 23.5 | 10.6 | 10.3 |
| $470 \Omega$ | 130 | 7.9 | 22.7 | 10.5 | 10.3 |

## APPLICATIONS InFORMATION

## Low Current Mode

Both mixer channels can be set to low current mode using the $I_{\text {SEL }}$ pin. This allows flexibility to choose a reduced current mode of operation when lower RF performance is acceptable. Figure 13 shows a simplified schematic of the $I_{\text {SEL }}$ pin interface. When $I_{\text {SEL }}$ is set low ( $<0.3 \mathrm{~V}$ ), both channels operate at nominal DC current. When $\mathrm{I}_{\mathrm{SEL}}$ is set high ( $>2.5 \mathrm{~V}$ ), the DC currents in both channels are reduced, thus reducing power consumption. The performance in low power mode and normal power mode are compared in Table 6.


Figure 13. ISEL Interface Schematic

Table 6. Performance Comparison Between Different Power Modes RF $=1950 \mathrm{MHz}$, Low Side LO, IF $=190 \mathrm{MHz}, \mathrm{ENA}=$ ENB $=$ High

| $\mathbf{I}_{\text {SEL }}$ | $\mathbf{I}_{\text {TOTAL }}$ <br> $(\mathbf{m A})$ | $\mathbf{G}_{\mathbf{C}}$ <br> $(\mathbf{d B})$ | IIP3 <br> $(\mathbf{d B m})$ | $\mathbf{P 1 d B}$ <br> $(\mathbf{d B m})$ | $\mathbf{N F}$ <br> $(\mathbf{d B})$ |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Low | 382 | 8.5 | 26.2 | 10.7 | 9.9 |
| High | 239 | 7.2 | 21.4 | 10.7 | 10.3 |

## Enable Interface

Figure 14 shows a simplified schematic of the ENA pin interface (ENB is identical). To enable channel A, the ENA voltage must be greater than 2.5 V . If the enable function is not required, the enable pin can be connected directly to $\mathrm{V}_{\mathrm{CC}}$. The voltage at the enable pin should never exceed the power supply voltage $\left(\mathrm{V}_{\mathrm{CC}}\right)$ by more than 0.3 V . If this should occur, the supply current could be sourced through the ESD diode, potentially damaging the IC.


Figure 14. ENA Interface Schematic
The Enable pins must be pulled high or low. If left floating, the on/off state of the IC will be indeterminate. If a three-state condition can exist at the enable pins, then a pull-up or pull-down resistor must be used.

## Supply Voltage Ramping

Fast ramping of the supply voltage can cause a current glitch in the internal ESD protection circuits. Depending on the supply inductance, this could result in a supply voltage transient that exceeds the maximum rating. A supply voltage ramp time of greater than 1 ms is recommended.

## Spurious Output Levels

Mixer spurious output levels versus harmonics of the RF and LO are tabulated in Table 7. The spur levels were measured on a standard evalution board using the test circuit shown in Figure 1. The spur frequencies can be calculated using the following equation:

$$
f_{S P U R}=\left(M \bullet f_{R F}\right)-\left(N \bullet f_{L O}\right)
$$

Table 7. IF Output Spur Levels (dBc)
$R F=1950 \mathrm{MHz}, \mathrm{P}_{\mathrm{RF}}=-3 \mathrm{dBm}, \mathrm{P}_{\mathrm{LO}}=0 \mathrm{OBm}, \mathrm{P}_{\mathrm{IF}} 190 \mathrm{MHz}$, Low Side LO, $\mathrm{V}_{\text {CC }}=3.3 \mathrm{~V}, \mathrm{~V}_{\text {CCIF }}=3.3 \mathrm{~V}$, ENA $=$ ENB $=$ High, $\mathrm{I}_{\text {SEL }}=$ LOW, $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$

| N |  |  |  |  |  |  |  |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| M |  | 0 | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 |
|  | 0 |  | -41 | -54 | -64 | -84 | -66 | -74 | -75 | -81 | -84 |
|  | 1 | -49 | 0 | -56 | -42 | -68 | -77 | -75 | -70 | * | -92 |
|  | 2 | -82 | -83 | -70 | -77 | * | * | * | * | * | * |
|  | 3 | * | -88 | * | -71 | * | * | * | * | * | * |
|  | 4 | * | * | * | * | * | * | * | * | * | * |
|  | 5 | * | * | * | * | * | * | * | * | * | * |
|  | 6 |  | * | * | * | * | * | * | * | * | * |
|  | 7 |  |  | * | * | * | * | * | * | -84 | * |

## UH Package

24-Lead Plastic QFN ( $5 \mathrm{~mm} \times 5 \mathrm{~mm}$ )
(Reference LTC DWG \# 05-08-1747 Rev A)


RECOMMENDED SOLDER PAD LAYOUT APPLY SOLDER MASK TO AREAS THAT ARE NOT SOLDERED


NOTE:

1. DRAWING IS NOT A JEDEC PACKAGE OUTLINE
2. DRAWING NOT TO SCALE
3. ALL DIMENSIONS ARE IN MILLIMETERS
4. DIMENSIONS OF EXPOSED PAD ON BOTTOM OF PACKAGE DO NOT INCLUDE

MOLD FLASH. MOLD FLASH, IF PRESENT, SHALL NOT EXCEED 0.20 mm ON ANY SIDE
5. EXPOSED PAD SHALL BE SOLDER PLATED
6. SHADED AREA IS ONLY A REFERENCE FOR PIN 1 LOCATION ON THE TOP AND BOTTOM OF PACKAGE

## TYPICAL APPLICATION

Lowpass IF Matching, Low Side LO, $\mathrm{V}_{\text {CC }}=3.3 \mathrm{~V}, \mathrm{~V}_{\text {CCIF }}=3.3 \mathrm{~V}$, ENA $=\mathrm{ENB}=$ High, $\mathrm{I}_{\text {SEL }}=$ Low, $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$, $P_{\mathrm{L} 0}=0 \mathrm{dBm}, \mathrm{P}_{\mathrm{RF}}=-3 \mathrm{dBm}(-3 \mathrm{dBm} /$ Tone for Two-Tone IIP3 Tests, $\Delta \mathrm{f}=2 \mathrm{MHz}$ ), IF $=190 \mathrm{MHz}$


## RELATGD PARTS

| PART NUMBER | DESCRIPTION | COMMENTS |
| :---: | :---: | :---: |
| Infrastructure |  |  |
| LT5527 | 400MHz to 3.7GHz, 5V Downconverting Mixer | 2.3dB Gain, 23.5dBm IIP3 and 12.5dB NF at 1900MHz, 5V/78mA Supply |
| LT5557 | 400MHz to 3.8GHz, 3.3V Downconverting Mixer | 2.9dB Gain, 24.7dBm IIP3 and 11.7dB NF at 1950MHz, 3.3V/82mA Supply |
| LTC6416 | 2GHz 16-Bit ADC Buffer | 40.25 dBm OIP3 to 300MHz, Programmable Fast Recovery Output Clamping |
| LTC6412 | 31dB Linear Analog VGA | 35 dBm OIP3 at 240 MHz , Continuous Gain Range -14 dB to 17dB |
| $\begin{aligned} & \text { LTC5540/LTC5541/ } \\ & \text { LTC5542/LTC5543 } \end{aligned}$ | 600MHz to 4GHz Downconverting Mixer Family | 8dB Gain, >25dBm IIP3, 10dB NF, 3.3V/200mA Supply |
| LT5554 | Ultralow Distort IF Digital VGA | 48dBm OIP3 at 200MHz, 2dB to 18dB Gain Range, 0.125dB Gain Steps |
| LT5578 | 400MHz to 2.7GHz Upconverting Mixer | 27 dBm OIP3 at 900 MHz , 24.2dBm at 1.95 GHz , Integrated RF Transformer |
| LT5579 | 1.5 GHz to 3.8 GHz Upconverting Mixer | 27.3dBm OIP3 at 2.14GHz, NF = 9.9dB, 3.3V Supply, Single-Ended LO and RF Ports |
| RF Power Detectors |  |  |
| LT5534 | 50MHz to 3GHz Log RF Power Detector with 60dB Dynamic Range | $\pm 1 \mathrm{~dB}$ Output Variation over Temperature, 38ns Response Time, Log Linear Response |
| LT5581 | 6GHz Low Power RMS Detector | 40dB Dynamic Range, $\pm 1 \mathrm{~dB}$ Accuracy Over Temperature, 1.5 mA Supply Current |
| LTC5583 | Dual 6GHz RMS Power Detector Measures VSWR | 40MHz to 6GHz, Up to 60dB Dynamic Range, >40dB Channel-to-Channel Isolation, Difference Output for VSWR Measurement |
| ADCs |  |  |
| LTC2285 | 14-Bit, 125Msps Dual ADC | 72.4 dB SNR, >88dB SFDR, 790 mW Power Consumption |
| LTC2185 | 16-Bit, 125Msps Dual ADC Ultralow Power | 76.8dB SNR, 185mW/Channel Power Consumption |
| LTC2242-12 | 12-Bit, 250Msps ADC | 65.4dB SNR, 78dB SFDR, 740 mW Power Consumption |
|  |  | 55919 |
| $\sum \bigcirc \underset{\substack{\text { Line } \\ 1630 \\(408)}}{4}$ | ar Technology Corporation McCarthy Blvd., Milpitas, CA 95035-7417 2-1900 • FAX: (408) 434-0507 • www.linear.com |  |

